

ZXTN25012EFL 12V, SOT23, NPN low power transistor

Summary

 $BV_{CEO} > 12V$

 $BV_{ECO} > 4.5V$

 $h_{FE} > 500$

 $I_{C(cont)} = 2A$

V_{CE(sat)} < 65 mV @ 1A

 $R_{CE(sat)} = 46 \text{ m}\Omega$

 $P_D = 350 \text{mW}$



Advanced process capability has been used to achieve high current gain hold up making this device ideal for applications requiring high pulse currents.

Features

- · High peak current
- · Low saturation voltage
- · 6V reverse blocking voltage

Applications

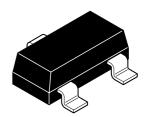
- · MOSFET and IGBT gate driving
- · DC-DC conversion
- · LED driving
- Interface between low voltage IC's and load

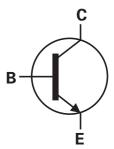
Ordering information

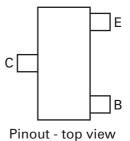
Device	Reel size	Tape width	Quantity	
	(inches)	(mm)	per reel	
ZXTN25012EFLTA	7	8	3000	

Device marking

1B6







Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	20	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-collector voltage	V _{ECO}	4.5	V
Emitter-base voltage	V _{EBO}	7	V
Continuous collector current ^(a)	I _C	2	Α
Base current	I _B	500	mA
Peak pulse current	I _{CM}	15	Α
Power dissipation @ T _{amb} =25°C ^(a)	P _D	350	mW
Linear derating factor		2.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	- 55 to 150	°C

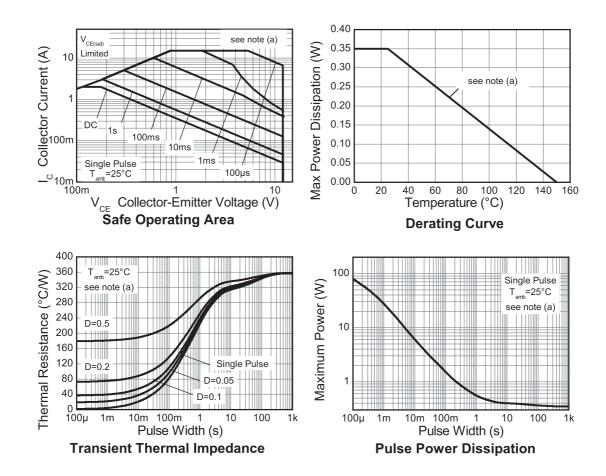
Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	357	°C/W

NOTES:

⁽a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



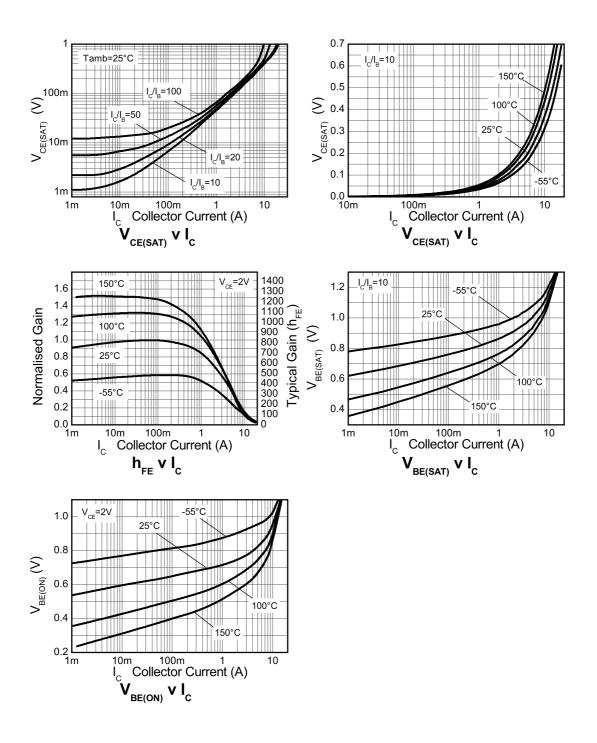
Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	20	40		V	$I_C = 100 \mu A$
Collector-emitter breakdown voltage	BV _{CEO}	12	17		V	I _C = 10mA ^(*)
Emitter-base breakdown voltage	BV _{EBO}	7	8.3		V	$I_E = 100 \mu A$
Emitter-collector breakdown voltage (reverse blocking)	BV _{ECX}	6	8		V	I_E = 100μA, $R_{BC} \le 1k\Omega$ or 0.25v > V_{BC} > -0.25V
Emitter-collector breakdown voltage (base open)	BV _{ECO}	4.5	5.5		V	$I_E = 100 \mu A$,
Collector cut-off current	I _{CBO}		<1	50	nA	V _{CB} = 16V
				20	μΑ	$V_{CB} = 16V, T_{amb} = 100^{\circ}C$
Emitter-base cut-off current	I _{EBO}		<1	50	nA	V _{EB} = 5.6V
Collector-emitter saturation	V _{CE(sat)}		50	65	mV	$I_C = 1A$, $I_B = 100 \text{mA}^{(*)}$
voltage			70	85	mV	$I_C = 1A$, $I_B = 10mA^{(*)}$
			105	130	mV	$I_C = 2A$, $I_B = 40mA^{(*)}$
			235	300	mV	$I_C = 5A$, $I_B = 100 \text{mA}^{(*)}$
Base-emitter saturation voltage	V _{BE(sat)}		830	950	mV	$I_C = 2A$, $I_B = 40mA^{(*)}$
Base-emitter turn-on voltage	V _{BE(on)}		745	850	mV	$I_C = 2A, V_{CE} = 2V^{(*)}$
Static forward current transfer ratio	h _{FE}	500	800	1500		I _C = 10mA, V _{CE} = 2V ^(*)
ratio		500	700			$I_C = 1A, V_{CE} = 2V^{(*)}$
		370	575			$I_C = 2A, V_{CE} = 2V^{(*)}$
		210	335			$I_C = 5A, V_{CE} = 2V^{(*)}$
		30	55			$I_C = 15A, V_{CE} = 2V^{(*)}$
Transition frequency	f _T		260		MHz	I _C = 50mA, V _{CE} = 10V f = 100MHz
Output capacitance	C _{obo}		25	35	pF	V _{CB} = 10V, f = 1MHz ^(*)
Delay time	t _(d)		71		ns	V _{CC} = 10V
Rise time	t _(r)		70		ns	$I_C = 1A$,
Storage time	t _(s)		233		ns	I _{B1} = I _{B2} = 10mA
Fall time	t _(f)		72		ns	

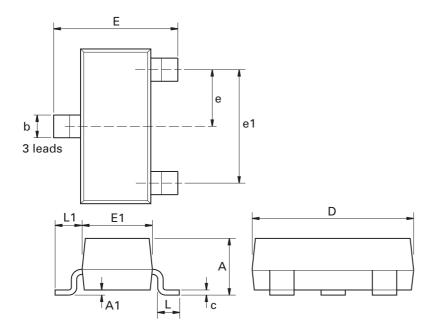
NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

Typical characteristics



Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
Α	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.120	0.003	0.008	L	0.25	0.62	0.018	0.024
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.0375	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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